

# EMZ1DXV6T1, EMZ1DXV6T5

## Dual General Purpose Transistors

### NPN/PNP Dual (Complementary)

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-563 which is designed for low power surface mount applications.

#### Features

- Lead-Free Solder Plating
- Low  $V_{CE(SAT)}$ ,  $< 0.5$  V
- These are Pb-Free Devices

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-60	V
Collector-Base Voltage	$V_{CBO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-6.0	V
Collector Current - Continuous	$I_C$	-100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	357 (Note 1) 2.9 (Note 1)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 1)	$^\circ\text{C}/\text{W}$
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	500 (Note 1) 4.0 (Note 1)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	250 (Note 1)	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

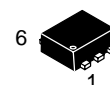
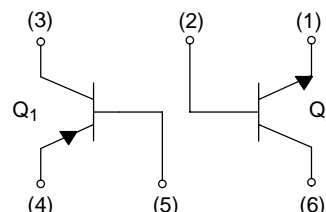
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 @ Minimum Pad.



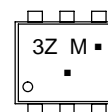
ON Semiconductor®

<http://onsemi.com>



SOT-563  
CASE 463A  
STYLE 1

#### MARKING DIAGRAM



3Z = Specific Device Code  
M = Month Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# EMZ1DXV6T1, EMZ1DXV6T5

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Q1: PNP</b>					
Collector-Base Breakdown Voltage (I <sub>C</sub> = -50 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-60	-	-	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-50	-	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = -50 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)EBO</sub>	-6.0	-	-	Vdc
Collector-Base Cutoff Current (V <sub>CB</sub> = -30 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	-0.5	nA
Emitter-Base Cutoff Current (V <sub>EB</sub> = -5.0 Vdc, I <sub>B</sub> = 0)	I <sub>EBO</sub>	-	-	-0.5	μA
Collector-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = -50 mAdc, I <sub>B</sub> = -5.0 mAdc)	V <sub>CE(sat)</sub>	-	-	-0.5	Vdc
DC Current Gain (Note 2) (V <sub>CE</sub> = -6.0 Vdc, I <sub>C</sub> = -1.0 mAdc)	h <sub>FE</sub>	120	-	560	-
Transition Frequency (V <sub>CE</sub> = -12 Vdc, I <sub>C</sub> = -2.0 mAdc, f = 30 MHz)	f <sub>T</sub>	-	140	-	MHz
Output Capacitance (V <sub>CB</sub> = -12 Vdc, I <sub>E</sub> = 0 Adc, f = 1 MHz)	C <sub>OB</sub>	-	3.5	-	pF

## Q2: NPN

Collector-Base Breakdown Voltage (I <sub>C</sub> = 50 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	-	-	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 50 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)EBO</sub>	7.0	-	-	Vdc
Collector-Base Cutoff Current (V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	0.5	μA
Emitter-Base Cutoff Current (V <sub>EB</sub> = 7.0 Vdc, I <sub>B</sub> = 0)	I <sub>EBO</sub>	-	-	0.5	μA
Collector-Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)	V <sub>CE(sat)</sub>	-	-	0.4	Vdc
DC Current Gain (Note 3) (V <sub>CE</sub> = 6.0 Vdc, I <sub>C</sub> = 1.0 mAdc)	h <sub>FE</sub>	120	-	560	-
Transition Frequency (V <sub>CE</sub> = 12 Vdc, I <sub>C</sub> = 2.0 mAdc, f = 30 MHz)	f <sub>T</sub>	-	180	-	MHz
Output Capacitance (V <sub>CB</sub> = 12 Vdc, I <sub>C</sub> = 0 Adc, f = 1 MHz)	C <sub>OB</sub>	-	2.0	-	pF

2. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

3. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

## ORDERING INFORMATION

Device	Package	Shipping†
EMZ1DXV6T1	SOT-563*	4000 Units / Tape & Reel
EMZ1DXV6T1G	SOT-563*	4000 Units / Tape & Reel
EMZ1DXV6T5	SOT-563*	8000 Units / Tape & Reel
EMZ1DXV6T5G	SOT-563*	8000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*This package is inherently Pb-Free.

# EMZ1DXV6T1, EMZ1DXV6T5

## TYPICAL ELECTRICAL CHARACTERISTICS – Q1, PNP

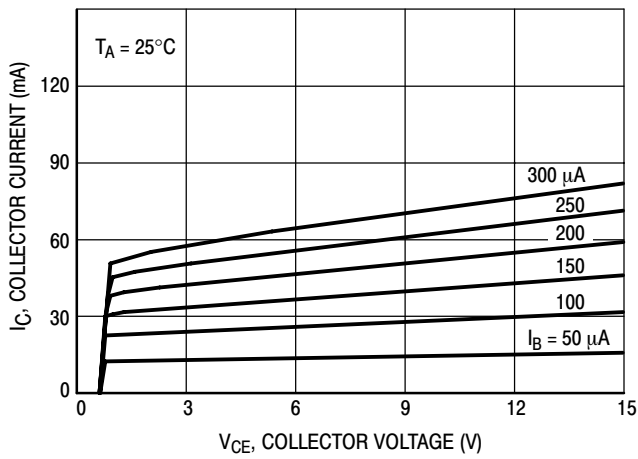


Figure 1.  $I_C - V_{CE}$

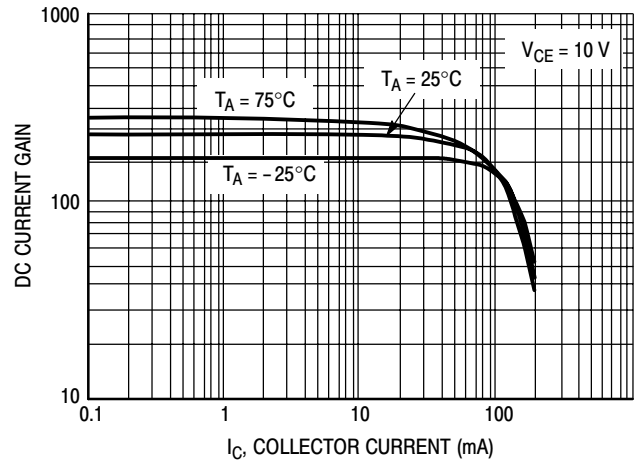


Figure 2. DC Current Gain

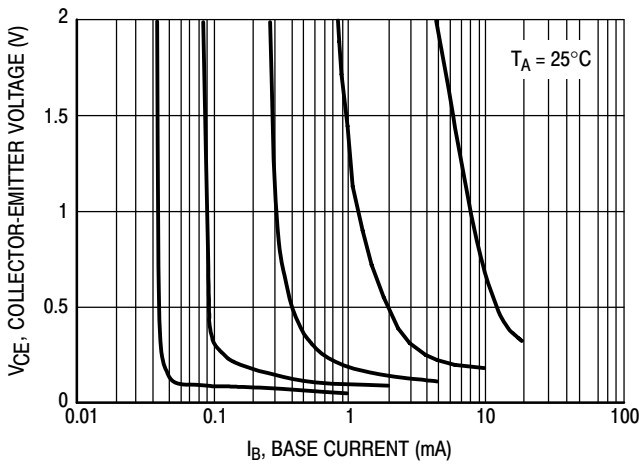


Figure 3. Collector Saturation Region

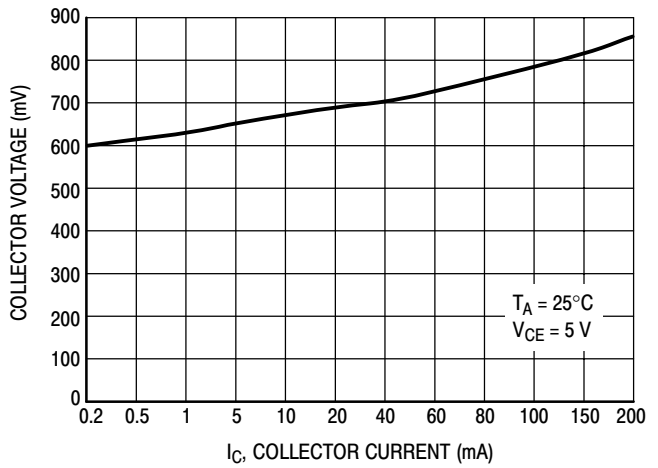


Figure 4. On Voltage

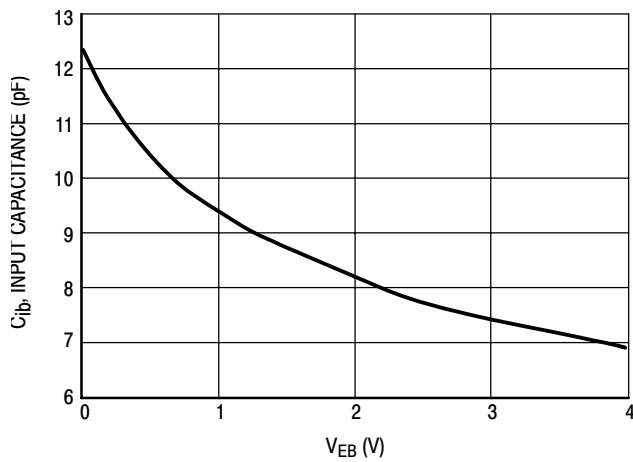


Figure 5. Capacitance

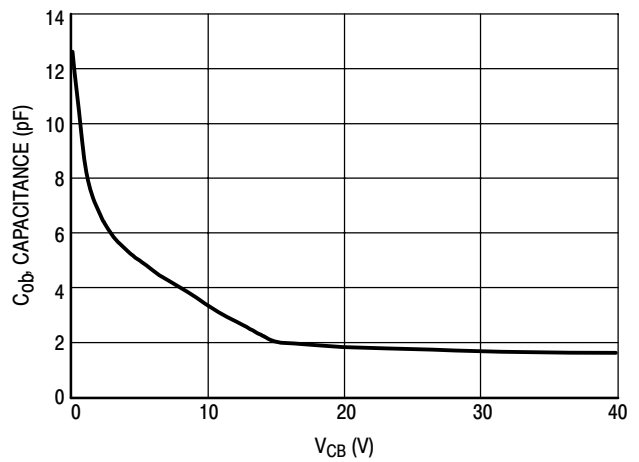


Figure 6. Capacitance

# EMZ1DXV6T1, EMZ1DXV6T5

## TYPICAL ELECTRICAL CHARACTERISTICS – Q2, NPN

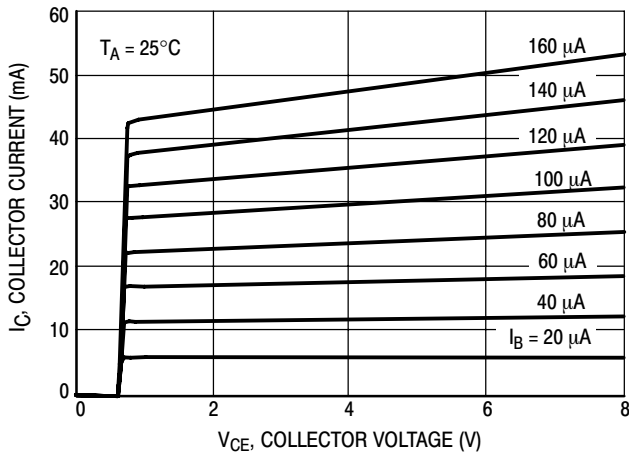


Figure 1.  $I_C - V_{CE}$

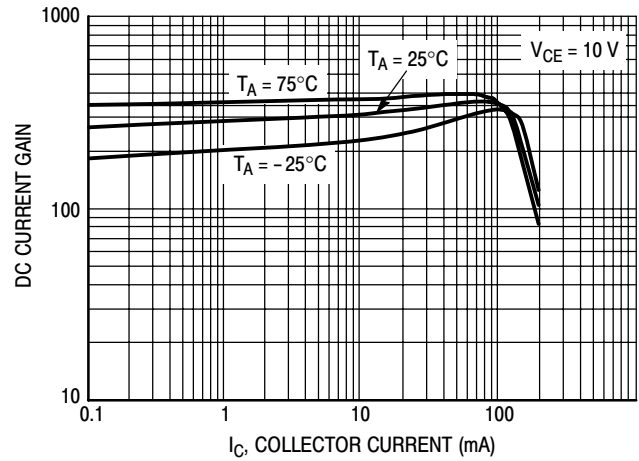


Figure 2. DC Current Gain

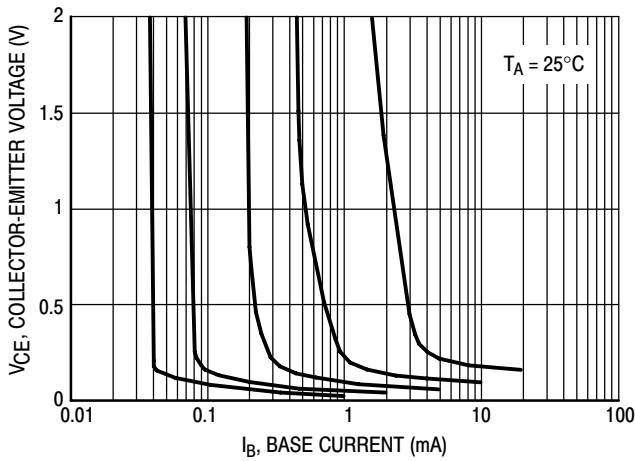


Figure 3. Collector Saturation Region

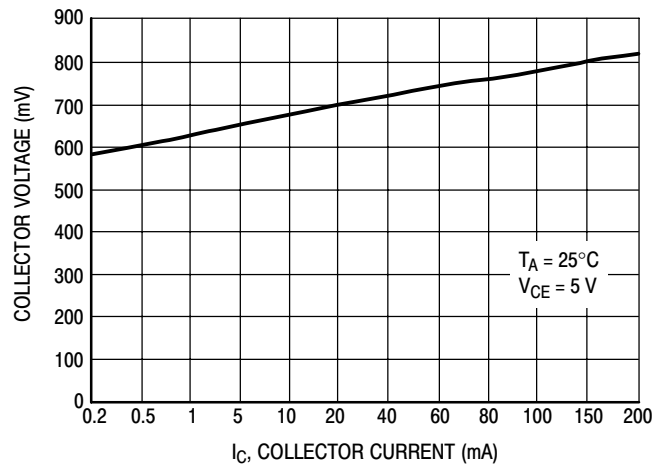


Figure 4. On Voltage

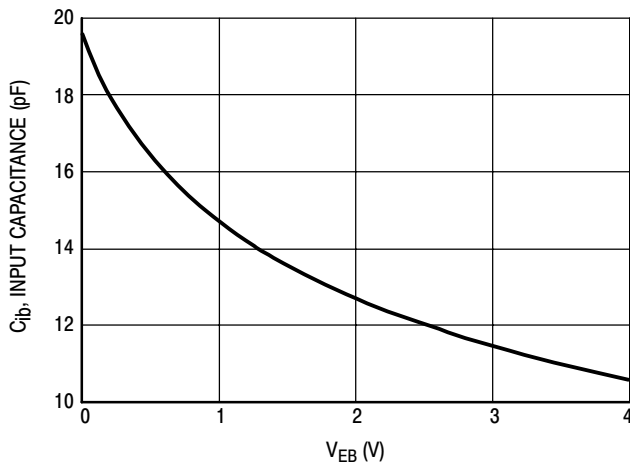


Figure 5. Capacitance

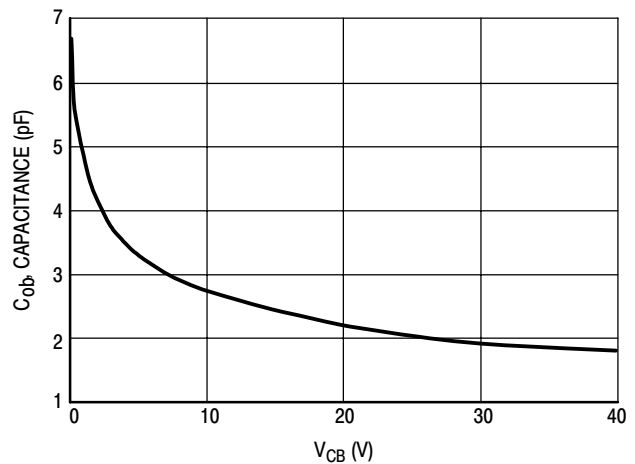


Figure 6. Capacitance

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

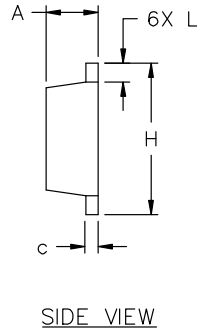
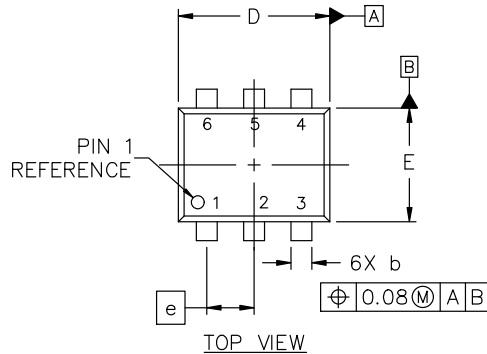


**SOT-563-6 1.60x1.20x0.55, 0.50P**  
**CASE 463A**  
**ISSUE J**

DATE 15 FEB 2024

**NOTES:**

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30

**STYLE 1:**  
 PIN 1. EMITTER 1  
 2. BASE 1  
 3. COLLECTOR 2  
 4. EMITTER 2  
 5. BASE 2  
 6. COLLECTOR 1

**STYLE 2:**  
 PIN 1. EMITTER 1  
 2. EMITTER 2  
 3. BASE 2  
 4. COLLECTOR 2  
 5. BASE 1  
 6. COLLECTOR 1

**STYLE 3:**  
 PIN 1. CATHODE 1  
 2. CATHODE 1  
 3. ANODE/ANODE 2  
 4. CATHODE 2  
 5. CATHODE 2  
 6. ANODE/ANODE 1

**STYLE 4:**  
 PIN 1. COLLECTOR  
 2. COLLECTOR  
 3. BASE  
 4. EMITTER  
 5. COLLECTOR  
 6. COLLECTOR

**STYLE 5:**  
 PIN 1. CATHODE  
 2. CATHODE  
 3. ANODE  
 4. ANODE  
 5. CATHODE  
 6. CATHODE

**STYLE 6:**  
 PIN 1. CATHODE  
 2. ANODE  
 3. CATHODE  
 4. CATHODE  
 5. CATHODE  
 6. CATHODE

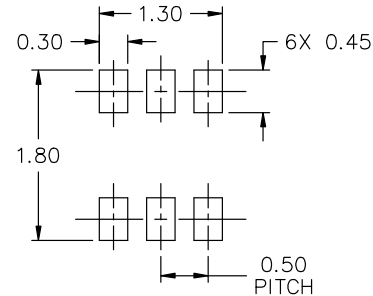
**STYLE 7:**  
 PIN 1. CATHODE  
 2. ANODE  
 3. CATHODE  
 4. CATHODE  
 5. ANODE  
 6. CATHODE

**STYLE 8:**  
 PIN 1. DRAIN  
 2. DRAIN  
 3. GATE  
 4. SOURCE  
 5. DRAIN  
 6. DRAIN

**STYLE 9:**  
 PIN 1. SOURCE 1  
 2. GATE 1  
 3. DRAIN 2  
 4. SOURCE 2  
 5. GATE 2  
 6. DRAIN 1

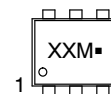
**STYLE 10:**  
 PIN 1. CATHODE 1  
 2. N/C  
 3. CATHODE 2  
 4. ANODE 2  
 5. N/C  
 6. ANODE 1

**STYLE 11:**  
 PIN 1. EMITTER 2  
 2. BASE 2  
 3. COLLECTOR 1  
 4. EMITTER 1  
 5. BASE 1  
 6. COLLECTOR 2



\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
 M = Month Code  
 ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

<b>DOCUMENT NUMBER:</b>	<b>98AON11126D</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SOT-563-6 1.60x1.20x0.55, 0.50P</b>	<b>PAGE 1 OF 1</b>

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at [www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)